

10/586581

IAP11 Rec'd PCT/PTO 19 JUL 2006

Combined Form PTO/SB/08A&B				Complete if Known	
				Application Number	Not yet assigned
				Confirmation Number	
				Filing Date	July 19, 2006
				First Named Inventor	Tsuguo FUKUDA et al.
				Art Unit	
				Examiner Name	
Sheet	1	of	1	Attorney Docket Number	062697

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. <sup>1</sup>	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document
		Number	Kind Code <sup>2</sup> (if known)		
/MC/	1	US 6,273,948	B1	8/14/2001	Porowski et al.
/MC/	2	US 6,270,569	B1	8/7/2001	Shibata et al.
/MC/	3	US 6,592,663	B1	7/15/2003	Sarayama et al.
/MC/	4	US 5,363,799		11/15/1994	Yonehara et al.
/MC/	5	US 2004/0144300	A1	7/29/2004	Kitaoka et al.

FOREIGN PATENT DOCUMENTS					
Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document
		Country Code <sup>3</sup>	Number <sup>4</sup>		
/MC/	6	JP	56-160400	A	12/10/1981
/MC/	7	JP	1-132117	A	5/24/1989
/MC/	8	JP	2004-244307	A	9/2/2004
/MC/	9	JP	2001-131741	A	5/15/2001

NON PATENT LITERATURE DOCUMENTS					
Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city, and/or country where published.			Translation <sup>6</sup>
/MC/	10	M.K. KELLY et al., "Optical patterning of GaN films", Appl. Phys. Lett. 69 (12), 16 September 1996			
/MC/	11	W.S. WONG et al., "Fabrication of thin-film InGaN light-emitting diode membranes by laser lift-off", Applied Physics Letters, Volume 75, Number 10, 6 September 1999			
/MC/	12	TAKAYUKI INOUE et al., "Growth of Bulk GaN Single Crystals by the Pressure-Controlled...", Central R&D Laboratory, Japan Energy Corporation, Faculty of Engineering, Yamaguchi University, May 15, 2000			
/MC/	13	S. POROWSKI et al., "Thermodynamical properties of III-V nitrides and crystal growth of...", Journal of Crystal Growth 178 (1997) 174-188			
/MC/	14	International Search Report mailed April 5, 2005 of International Application PCT/JP2005/000696			

Examiner Signature	/Marissa Chaet/	Date Considered	08/09/2007
--------------------	-----------------	-----------------	------------

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<sup>1</sup>Applicant's unique citation designation number (optional). <sup>2</sup>See Kind Codes of USPTO Patent Documents at www.uspto.gov, MPEP 901.04 or in the comment box of this document. <sup>3</sup> Enter Office that issued the document, by the two-letter code (WIPO Standard ST. 3). <sup>4</sup>For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup>Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. <sup>6</sup>Applicant is to indicate here if English language Translation is attached.